



DMP3017SFV

30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C		
001/	$10m\Omega @ V_{GS} = -10V$	-40A		
-30V	18mΩ @ V _{GS} = -4.5V	-25A		

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

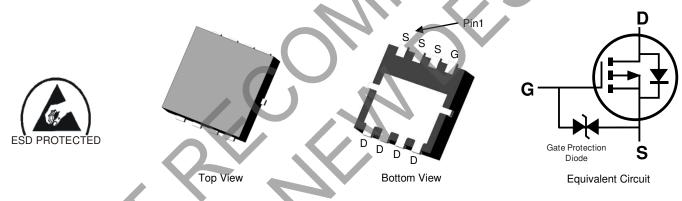
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} ensures on-state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
 Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (@3)
 - Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3017SFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMP3017SFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



<u>V1</u>7 = Product Type Marking Code <u>YYWW</u> = Date Code Marking <u>YY</u> = Last Two Digits of Year (ex: 17 = 2017) <u>WW</u> = Week Code (01 to 53)

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1 of 7 www.diodes.com



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V_{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	ID	-11.5 -9.4	А
Continuous Drain Current (Note 7) V_{GS} = -10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	ID	-40 -30	А
Maximum Continuous Body Diode Forward Current (Note 7)			ls	-30	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	I _{DM}	-80	А		
Pulsed Body Diode Forward Current (10µs Pulse,	I _{SM}	-80	A		
Avalanche Current (Note 8) L = 1mH			IAS	-14	А
Avalanche Energy (Note 8) L = 1mH			E _{AS}	104	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	Pb	0.94	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	134	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	Pp	1.94	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{eJA}	65	°C/W
Total Power Dissipation (Note 7)		PD	31	W
Thermal Resistance, Junction to Case (Note 7)		Rejc	4.0	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
DFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	-30	—		V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current	IDSS	Ŧ	Ţ	-1	μA	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±10	μA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-	-3.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance			8.5	10	mΩ	$V_{GS} = -10V, I_D = -11.5A$	
Static Drain-Source On-nesistance	R _{DS} (ON)		15	18		$V_{GS} = -4.5V, I_D = -8.5A$	
Diode Forward Voltage	V _{SD}		-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	2,246	_	pF		
Output Capacitance	Coss	_	352	_	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	294	_	pF		
Gate Resistance	Rg	_	5.1	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -5V)	Qg	_	20.5	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	41	_	nC		
Gate-Source Charge	Qgs	_	7.6	_	nC	V _{DS} = -15V, I _D = -11.5A	
Gate-Drain Charge	Q _{gd}	_	8.0	_	nC		
Turn-On Delay Time	t _{D(ON)}		7.5		ns		
Turn-On Rise Time	t _R	_	15.4	_	ns	V _{DD} = -15V, V _{GS} = -10V,	
Turn-Off Delay Time	t _{D(OFF)}	_	45.6	_	ns	R _G = 6Ω, I _D = -11.5A	
Turn-Off Fall Time	t _F	_	36.8	_	ns	7	
Reverse Recovery Time	t _{RR}	_	20		ns		
Reverse Recovery Charge	Q _{RR}	-	9.5		nC	l _S = -11.5A, dl/dt = 100A/µs	

Notes:

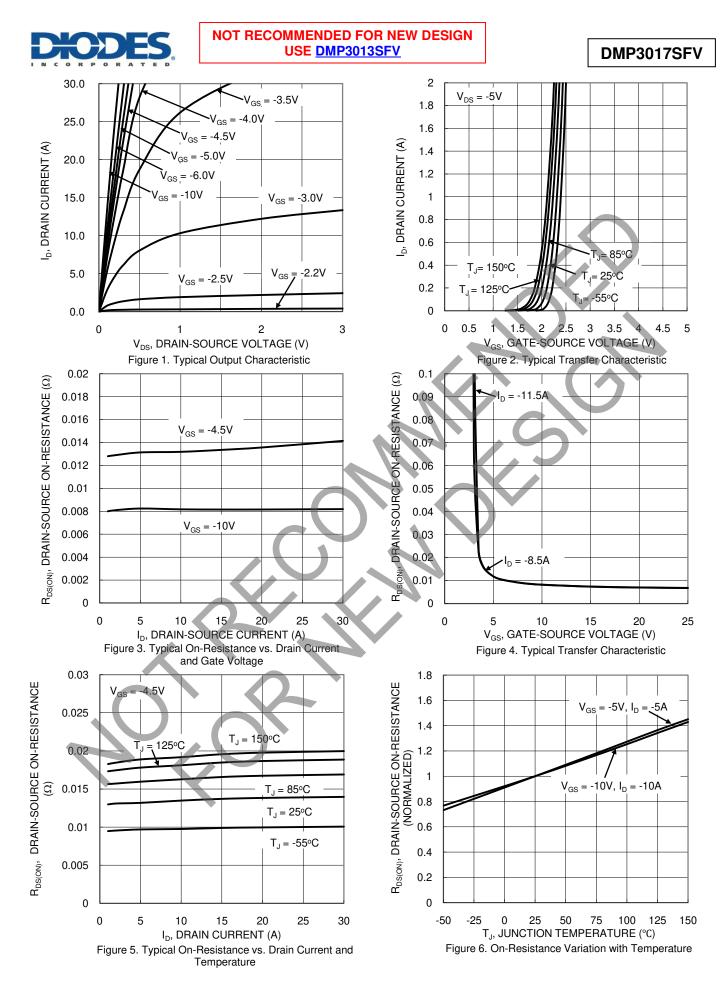
Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

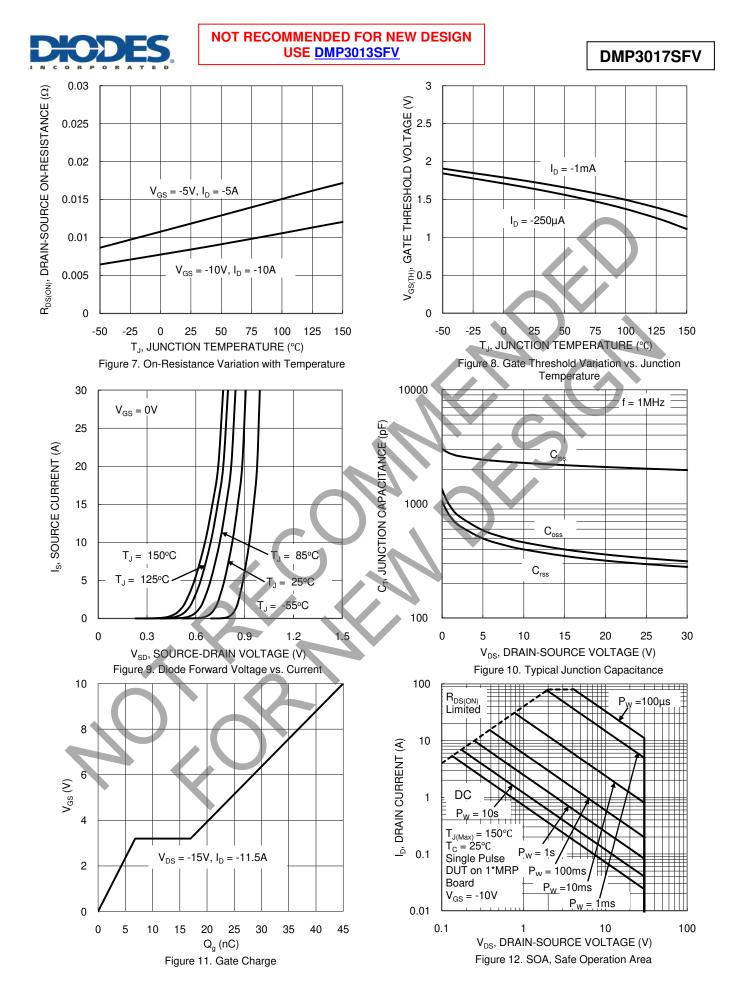
7. Thermal resistance from junction to soldering point (on the exposed drain pad).

8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

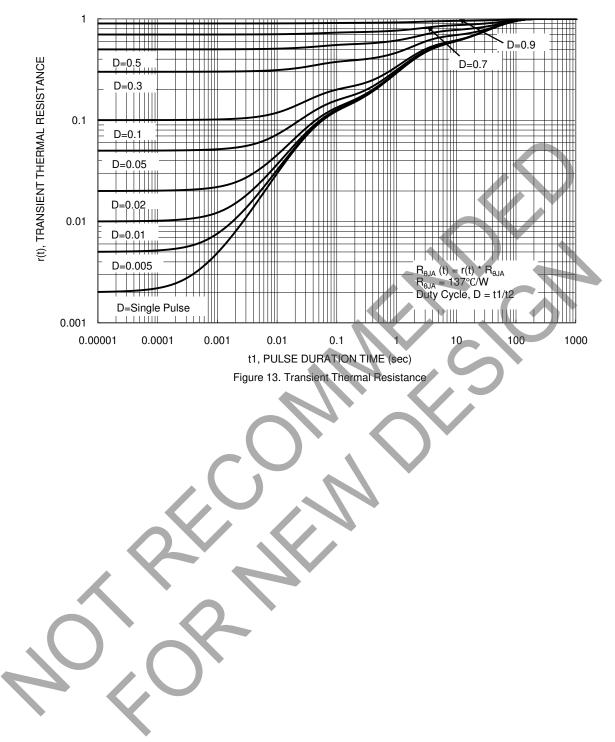






NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP3013SFV</u>

DMP3017SFV

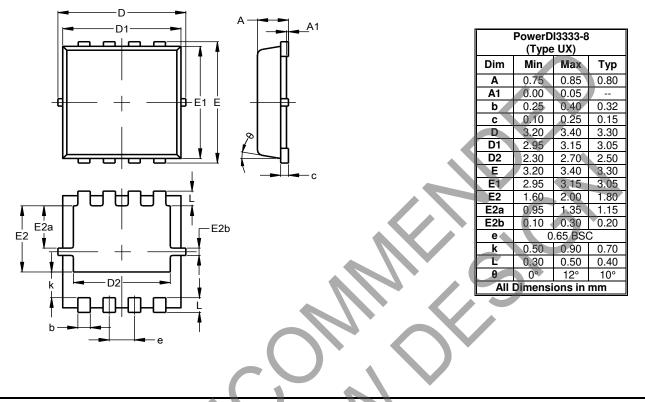




Package Outline Dimensions

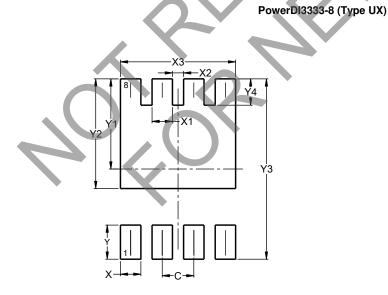
Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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